

1. Scope :

This specification applies to NPN silicon phototransistor twin chips ,
Device No. ST-0124T.

2. Structure :

- 2-1. Planar type.
- 2-2. Electrodes :
 - N (Collector) side : Gold alloy.
 - P (Base) side : Aluminum alloy.
 - N (Emitter) side : Aluminum alloy.

3. Size :

- 3-1. Chip size : 24 mils × 48 mils (0.610 mm × 1.220 mm).
- 3-2. Chip thickness : 7.0 ± 1.5 mils (0.178 ± 0.038 mm).
- 3-3. Active area : 17 mils × 17 mils (0.432 mm × 0.432 mm).
- 3-4. Pattern drawing : refer to the attached drawing.

4. Electrical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Collector-emitter Breakdown Voltage	BV_{CEO}	$I_C=100\mu A$ $I_B=0$	30		110	V
Emitter-collector Breakdown Voltage	BV_{ECO}	$I_E=100\mu A$ $I_B=0$	6.5			V
Collector dark current	I_{CEO}	$V_{CE}=20V$ $H=0mw/cm^2$			100	nA
Collector-emitter Saturation Voltage	$V_{CE(S)}$	$I_C=2mA$ $I_B=100\mu A$			0.2	V
Rise/Fall Time	tR/tF	$V_{CE}=5V$ $I_C=1mA$ $R_L=1000\Omega$		15/15		μS
Current gain	h_{FE}	$V_{CE}=5V$ $I_C=2mA$	500			
Collector-base Capacitance	C_{CB}	f=1MHZ $V_{CB}=3V$	5.4	6.4	7.4	PF

- hFE RANK A : 500 - 1000
- RANK B : 700 - 1400
- RANK C : 800 - 1800
- RANK D : 900 -

